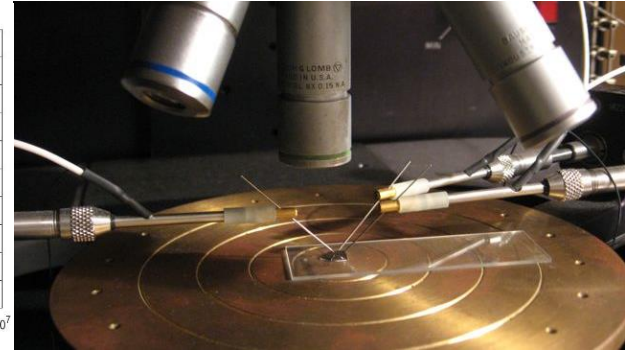
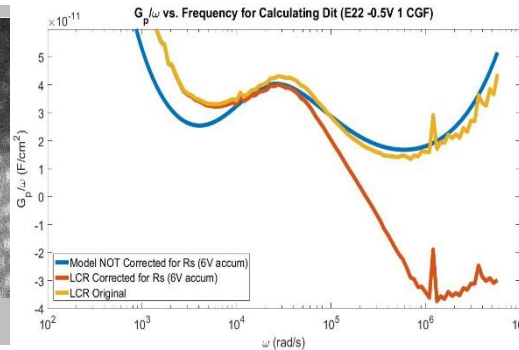


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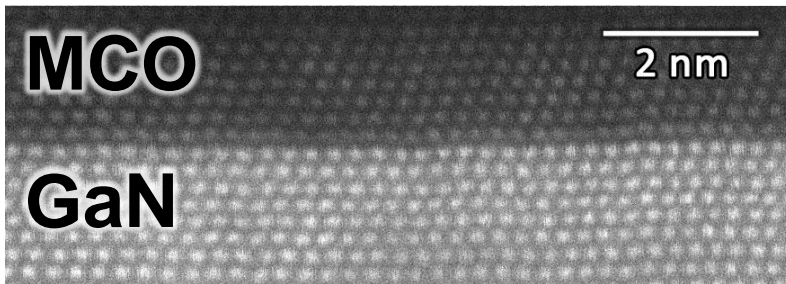
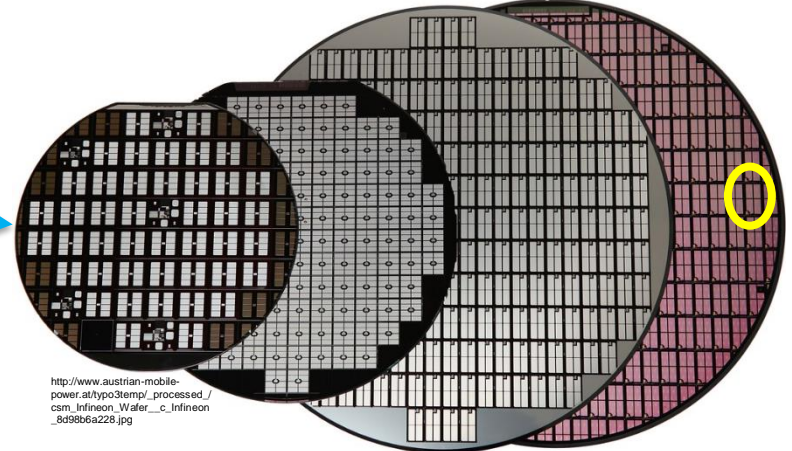
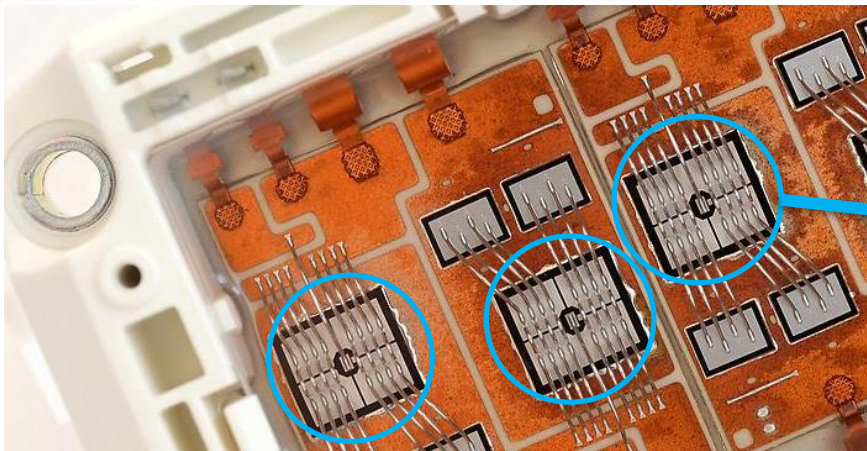
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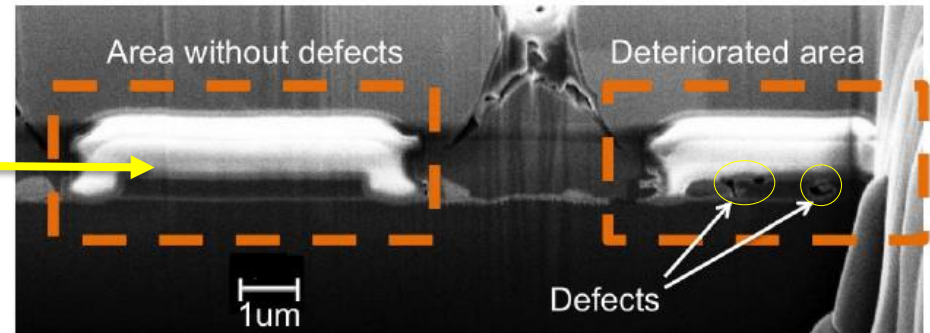


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Paisley *et al.*, J. Appl. Phys. **115**, 2014



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